

isc Silicon PNP Power Transistor

2SB514

DESCRIPTION

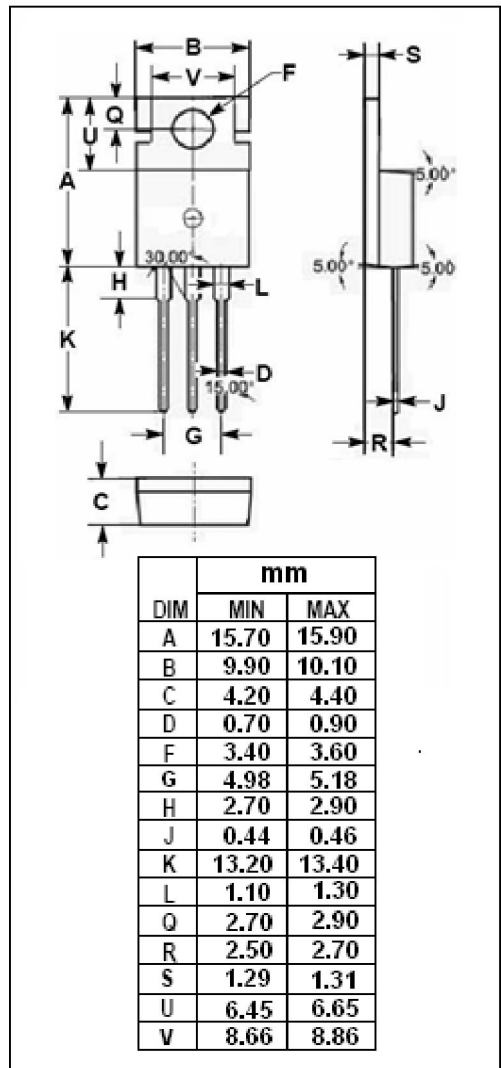
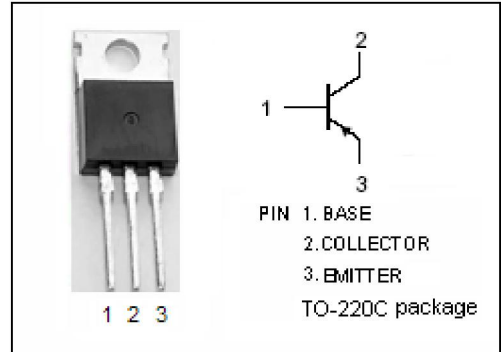
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -50V(\text{Min})$
- Low Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = -1.0V(\text{Max}) @ I_C = -2.0A$
- Complement to Type 2SD330

APPLICATIONS

- Suited for use in output stage of 10W AF power amplifier.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-5	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1.75	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	20	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon PNP Power Transistor**2SB514****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$			-1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -1\text{A}; V_{CE} = -5\text{V}$			-1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -20\text{V}; I_E = 0$			-100	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -4\text{V}; I_C = 0$			-1	mA
h_{FE-1}	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -2\text{V}$	40		320	
h_{FE-2}	DC Current Gain	$I_C = -0.1\text{A}; V_{CE} = -2\text{V}$	35			
f_T	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}; V_{CE} = -5\text{V}$		8		MHz

◆ **h_{FE-1} Classifications**

C	D	E	F
40-80	60-120	100-200	160-320